



JA11001700P50; 1100 MHz – 1700 MHz 100W AMPLIFIER

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Small Dimensions & Light Weight
- Forward/Reflected Power Monitorings
- Temperature and Current Monitorings
- Fast Switching Capability



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	1100-1700 MHz
Output Power:	100 W min. CW
Nominal Gain:	50 dB
Gain Flatness:	± 2 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1min.
DC Supply Voltage:	32 V
DC Current:	9.5 A Avg
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
7W2 DSUB:	A1) GND
	A2) 32 V
	1) Temp.
	2) Current
	3) Rev. Power
	4) Fwd. Power
	5) Enable

MECHANICAL SPECIFICATIONS

Size (mm) : 206.3 x 86.4 x 21.5
Weight : 800 gr.
Plating : Yellow Chromate

